

ABSTRACT OF THE DISCLOSURE

The invention comprises a lower electrode which is disposed in a processing chamber and holds a wafer W, and an exhaust ring mechanism disposed between the lower electrode and an inner wall of the processing chamber, wherein the exhaust ring mechanism has an exhaust ring, and a magnetic field forming section which forms a magnetic field parallel to the principal plane of the exhaust ring, and thereby preventing plasma leak from a plasma region to a non-plasma region by the formed magnetic field, and a plasma processing apparatus using the exhaust ring mechanism.